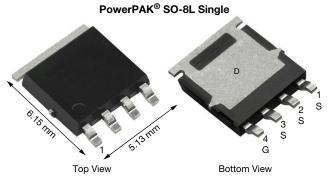
SQJ488EP



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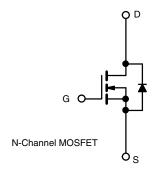
Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	100
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0210
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0258
I _D (A)	42
Configuration	Single



FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified ^d
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





HALOGEN

ORDERING INFORMATION

Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ488EP-T1-GE3

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless	otherwise noted	l)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage		V _{GS}	± 20	v	
Continuous Drain Current	T _C = 25 °C ª	1	42		
	T _C = 125 °C	I _D	24		
Continuous Source Current (Diode Conduction) ^a		۱ _S	60	А	
Pulsed Drain Current ^b		I _{DM}	170		
Single Pulse Avalanche Current		I _{AS}	5.8		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	1.68	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	P	83	w	
	T _C = 125 °C	P _D	27		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	
Soldering Recommendations (Peak Temperature) e, f			260	-0	

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	65	°C/W
Junction-to-Case (Drain)		R _{thJC}	1.8	0/10

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.
- e. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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	P. MAX.	MAX. U	MAX.	TYP.	MIN. TYP	T CONDITIONS	TES	SYMBOL	PARAMETER
$ \begin{array}{c c c c c c } \hline Gate-Source Threshold Voltage & V_{GS}(th) & V_{DS} = V_{GS}, \ l_{D} = 250 \ \mu A & 1.5 & 2.0 \\ \hline Gate-Source Leakage & I_{GSS} & V_{DS} = 0 \ V, \ V_{GS} = \pm 20 \ V & - & - \\ \hline \\ \hline \\ \hline \\ Zero \ Gate Voltage Drain Current & I_{DSS} & V_{DS} = 0 \ V, \ V_{DS} = 100 \ V, \ T_{J} = 125 \ ^{\circ}C & - & - \\ \hline \\ \hline \\ \hline \\ \hline \\ V_{GS} = 0 \ V & V_{DS} = 100 \ V, \ T_{J} = 125 \ ^{\circ}C & - & - \\ \hline \\ \hline \\ \hline \\ V_{GS} = 0 \ V & V_{DS} = 100 \ V, \ T_{J} = 125 \ ^{\circ}C & - & - \\ \hline \\ \hline \\ \hline \\ \hline \\ On-State Drain Current \ ^{a} & I_{D(on)} & V_{GS} = 10 \ V & V_{DS} = 100 \ V, \ T_{J} = 175 \ ^{\circ}C & - & - \\ \hline \\ \hline \\ \hline \\ \hline \\ On-State Drain Current \ ^{a} & I_{D(on)} & V_{GS} = 10 \ V & I_{D} = 7.1 \ A & - & 0.017 \\ \hline \\ \hline \\ \hline \\ Prain-Source On-State Resistance \ ^{a} & g_{fs} & V_{DS} = 15 \ V \ I_{D} = 6.4 \ A & - & 0.021 \\ \hline \\ \hline \\ \hline \\ \hline \\ \hline \\ \hline \\ V_{GS} = 10 \ V & I_{D} = 7.1 \ A \ T_{J} = 125 \ ^{\circ}C & - & - \\ \hline \\$					1			1	Static
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	-	-	-	-	100 -	= 0, I _D = 250 µA	V _{GS}	V _{DS}	Drain-Source Breakdown Voltage
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	0 2.5	2.5	2.5	2.0	1.5 2.0	= V _{GS} , I _D = 250 μΑ	V _{DS} =	V _{GS(th)}	Gate-Source Threshold Voltage
$ \begin{array}{ c c c } \hline V_{DS} = 0 \lor V_{DS} = 100 \lor, T_J = 125 \degree C & - & - & - & - & - & - & - & - & - &$	± 100	± 100	± 100	-		0 V, V _{GS} = ± 20 V	V _{DS} =	I _{GSS}	Gate-Source Leakage
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	1	1	1	-		V _{DS} = 100 V	$V_{GS} = 0 V$		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	50	50	50	-		V _{DS} = 100 V, T _J = 125 °C	$V_{GS} = 0 V$	I _{DSS}	Zero Gate Voltage Drain Current
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	150	150	150	-		$V_{DS} = 100 \text{ V}, \text{ T}_{\text{J}} = 175 ^{\circ}\text{C}$	$V_{GS} = 0 V$		-
$ \begin{array}{ c c c c c c } \hline Drain-Source On-State Resistance a & $V_{GS} = 4.5 V & $I_D = 6.4 A & $-$ & 0.021 \\ \hline $V_{GS} = 10 V & $I_D = 7.1 A, $T_J = 125 $^\circ$C$ & $-$ & $-$ \\ \hline $V_{GS} = 10 V & $I_D = 7.1 A, $T_J = 175 $^\circ$C$ & $-$ & $-$ \\ \hline $V_{GS} = 10 V & $I_D = 7.1 A, $T_J = 175 $^\circ$C$ & $-$ & $-$ & $-$ \\ \hline $V_{GS} = 10 V & $I_D = 7.1 A, $T_J = 175 $^\circ$C$ & $-$ & $-$ & $-$ \\ \hline $Dynamic b & $V_{DS} = 15 V, $I_D = 7.1 A & $-$ & 28 \\ \hline $Dynamic b & $V_{DS} = 15 V, $I_D = 7.1 A & $-$ & 28 \\ \hline $Dynamic b & $V_{DS} = 10 V & $V_{DS} = 50 V, $f = 1 MHz & $-$ & 372 \\ \hline $Total Gate Charge $^\circ$ & Q_{G} & $V_{GS} = 0 V & $V_{DS} = 50 V, $f = 1 MHz & $-$ & 44 \\ \hline $Total Gate Charge $^\circ$ & Q_{Gd} & $V_{GS} = 10 V & $V_{DS} = 50 V, $I_D = 15 A & $-$ & 2 \\ \hline $Gate -Drain Charge $^\circ$ & Q_{Gd} & $V_{GS} = 10 V & $V_{DS} = 50 V, $I_D = 15 A & $-$ & 2 \\ \hline $Gate Resistance R_{g} & $f = 1 MHz & 1.1 & 2.2 \\ \hline $Turn-On Delay Time $^\circ$ & $t_{d(orn)}$ & $V_{DD} = 50 V, $R_L = 5 Ω \\ \hline $Rise Time $^\circ$ & $t_{d(off)}$ & $V_{DD} = 50 V, $R_L = 5 Ω & $-$ & $-$ \\ \hline $I_D \cong 1 A, $V_{GSN} = 10 V, $R_g = 6 Ω & $-$ & 11 \\ \hline $I_D \cong 1 A, $V_{GSN} = 10 V, $R_g = 6 Ω & $-$ & 2 \\ \hline $I_D = 1 A, $V_{GSN} = 10 V, $R_g = 6 Ω & $-$ & 2 \\ \hline $I_D = 1 A, $V_{GSN} = 10 V, $R_g = 6 Ω & $-$ & 2 \\ \hline $I_D = 1 A, $V_{GSN} = 10 V, $R_g = 6 Ω & $-$ & 2 \\ \hline $I_D = 1 A, $V_{GSN} = 10 V, $R_g = 6 Ω & $-$ & 2 \\ \hline $I_D = 1 A, $V_{GSN} = 10 V, $R_g = 6 Ω & $-$ & 2 \\ \hline $I_D = 1 A, $V_{GSN} = 10 V, $R_g = 6 Ω & $-$ & 2 \\ \hline $I_D = 1 A, $V_{GSN} = 10 V, $R_g = 6 Ω & $-$ & 2 \\ \hline $I_D = 1 A, $V_{GSN} = 10 V, $R_g = 6 Ω & $-$ & 2 \\ \hline $I_D = 1 A, $V_{GSN} = 10 V, $R_g = 6 Ω & $-$ & 2 \\ \hline $I_D = 1 A, $V_{GSN} = 10 V, $R_g = 6 Ω & $-$ & 2 \\ \hline $I_D = 1 A, $V_{GSN} = 10 V, $R_g = 6 Ω & $-$ & 2 \\ \hline $I_D = 1 A, $V_{GSN} = 10 V, $R_g = 6 Ω & $-$ & 2 \\ \hline $I_D = 1 A \\ \hline $I_D = 1 A \\$	-	-	-	-	30 -	$V_{DS} \ge 5 V$	$V_{GS} = 10 V$	I _{D(on)}	On-State Drain Current ^a
$ \begin{array}{ c c c c c c c } \hline Prain-Source On-State Resistance a \\ \hline P_{DS(on)} & \hline V_{GS} = 10 \ V & I_D = 7.1 \ A, \ T_J = 125 \ ^{\circ}C & - & - \\ \hline V_{GS} = 10 \ V & I_D = 7.1 \ A, \ T_J = 175 \ ^{\circ}C & - & - \\ \hline P_{OS} = 10 \ V & I_D = 7.1 \ A, \ T_J = 175 \ ^{\circ}C & - & - \\ \hline P_{OS} = 10 \ V & I_D = 7.1 \ A, \ T_J = 175 \ ^{\circ}C & - & - \\ \hline P_{OS} = 10 \ V & I_D = 7.1 \ A, \ T_J = 175 \ ^{\circ}C & - & - \\ \hline P_{OS} = 10 \ V & I_D = 7.1 \ A, \ T_J = 175 \ ^{\circ}C & - & - \\ \hline P_{OS} = 10 \ V & I_D = 7.1 \ A, \ T_J = 175 \ ^{\circ}C & - & - \\ \hline P_{OS} = 10 \ V & I_D = 7.1 \ A, \ T_J = 175 \ ^{\circ}C & - & - \\ \hline P_{OS} = 10 \ V & I_D = 7.1 \ A, \ T_J = 175 \ ^{\circ}C & - & - \\ \hline P_{OS} = 10 \ V & I_D = 7.1 \ A, \ T_J = 175 \ ^{\circ}C & - & - \\ \hline P_{OS} = 10 \ V \ P_{OS} = 10 \ V \ P_{OS} = 50 \ V, \ f = 1 \ MHz & - & 11 \\ \hline P_{OS} = 10 \ V \ P_{OS} = 50 \ V, \ I_D = 15 \ A & - & 11 \\ \hline P_{OS} = 10 \ V \ P_{OS} = 50 \ V, \ I_D = 15 \ A & - & 11 \\ \hline P_{OS} = 10 \ V \ P_{OS} = 50 \ V, \ I_D = 15 \ A & - & 28 \\ \hline P_{OS} = 10 \ V \ P_{OS} = 50 \ V, \ I_D = 15 \ A & - & 28 \\ \hline P_{OS} = 10 \ V \ P_{OS} = 50 \ V, \ I_D = 15 \ A & - & 28 \\ \hline P_{OS} = 10 \ V \ P_{OS} = 50 \ V, \ I_D = 15 \ A & - & 28 \\ \hline P_{OS} = 10 \ V \ P_{OS} = 50 \ V, \ I_D = 15 \ A & - & 28 \\ \hline P_{OS} = 10 \ V \ P_{OS} = 50 \ V, \ I_D = 15 \ A & - & 28 \\ \hline P_{OS} = 10 \ V \ P_{OS} = 50 \ V, \ I_D = 15 \ A & - & 28 \\ \hline P_{OS} = 10 \ V \ P_{OS} = 50 \ V, \ I_D = 15 \ A & - & 28 \\ \hline P_{OS} = 10 \ V \ P_{OS} = 50 \ V, \ I_D = 15 \ A & - & 28 \\ \hline P_{OS} = 10 \ V \ P_{OS} = 50 \ V, \ P_{OS} = 50 \ V, \ P_{OS} = 6 \ \Omega & - & 44 \\ \hline P_{OS} = 111 \ P_{OS} = 10 \ V, \ P_{OS} = 6 \ \Omega & - & 111 \\ \hline P_{OS} = 1 \ A \ P_{OS} = 10 \ V, \ P_{OS} = 6 \ \Omega & - & 111 \\ \hline P_{OS} = 1 \ A \ P_{OS} = 10 \ V, \ P_{OS} = 6 \ \Omega & - & 111 \\ \hline P_{OS} = 1 \ A \ P_{OS} = 10 \ V, \ P_{OS} = 6 \ \Omega & - & - & 4. \\ \hline P_{OS} = 10 \ V \ P_{OS} = 10 \ V, \ P_{OS} = 10 \ V, \ P_{OS} = 10 \ V \ $	76 0.0210	0.0210	0.0210	0.0176	- 0.01	I _D = 7.1 A	$V_{GS} = 10 V$		
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	215 0.0258	0.0258	0.0258	0.0215	- 0.02	I _D = 6.4 A	$V_{GS} = 4.5 V$	Р	Drain Course On State Desistance a
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	0.0360	0.0360	0.0360	-		I _D = 7.1 A, T _J = 125 °C	V _{GS} = 10 V	R _{DS(on)}	Drain-Source On-State Resistance ª
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	0.0450	0.0450	0.0450	-		I _D = 7.1 A, T _J = 175 °C	$V_{GS} = 10 V$		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	3 -	-	-	28	- 28	V _{DS} = 15 V, I _D = 7.1 A		9 _{fs}	Forward Transconductance ^b
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $									Dynamic ^b
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	2 978	978	978	782	- 782			C _{iss}	Input Capacitance
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	2 462	462	462	372	- 372	V V _{DS} = 50 V, f = 1 MHz	$V_{GS} = 0 V$	C _{oss}	Output Capacitance
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	4 55	55	55	44	- 44				Reverse Transfer Capacitance
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	3 27	27	27	18	- 18			Qg	Total Gate Charge ^c
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	-	-	-	2	- 2	$V_{DS} = 50 \text{ V}, \text{ I}_{D} = 15 \text{ A}$	$V_{GS} = 10 V$	Q _{gs}	Gate-Source Charge
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	7 -	-	-	4.7	- 4.7			Q _{gd}	Gate-Drain Charge ^c
Rise Time ° t_r $V_{DD} = 50 \text{ V}, \text{ R}_L = 5 \Omega$ -11Turn-Off Delay Time ° $t_{d(off)}$ $I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, \text{ R}_g = 6 \Omega$ -20Fall Time ° t_f -4.6Source-Drain Diode Ratings and Characteristics b	2 3.3	3.3	3.3	2.2	1.1 2.2	f = 1 MHz		R _g	Gate Resistance
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	6	6	6	4	- 4			t _{d(on)}	Turn-On Delay Time ^c
Fall Time c tf - 4.6 Source-Drain Diode Ratings and Characteristics b - - -	1 16	16	16	11	- 11	DD / L		t _r	Rise Time ^c
Source-Drain Diode Ratings and Characteristics ^b) 30	30	30	20	- 20			t _{d(off)}	Turn-Off Delay Time °
	6 7	7	7	4.6	- 4.6			t _f	Fall Time ^c
Pulsed Current ^a I _{SM}								cteristics ^b	Source-Drain Diode Ratings and Chara
	128	128	128	-				I _{SM}	Pulsed Current ^a
Forward Voltage V_{SD} $I_F = 4.7 \text{ A}, V_{GS} = 0$ - 0.78	78 1.2	1.2	1.2	0.78	- 0.7	= 4.7 A, V _{GS} = 0	I _F =	V _{SD}	Forward Voltage

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

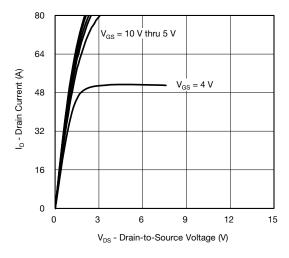
2



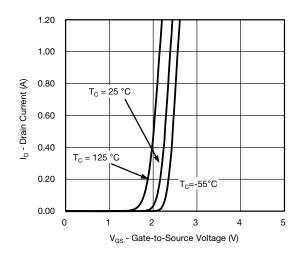
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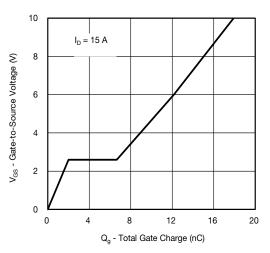
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



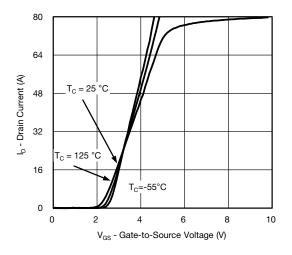
Output Characteristics



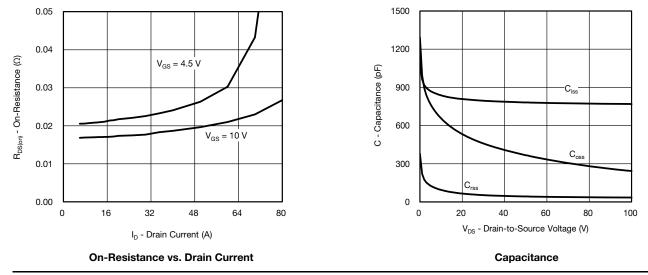
Transfer Characteristics



Gate Charge







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3

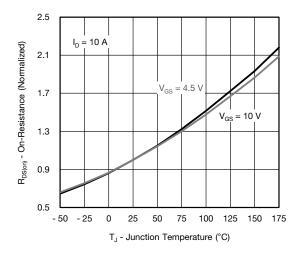
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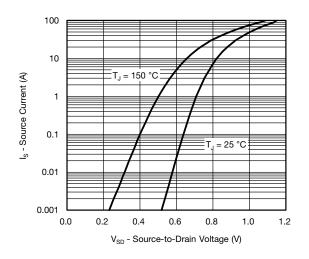
SQJ488EP

Vishay Siliconix

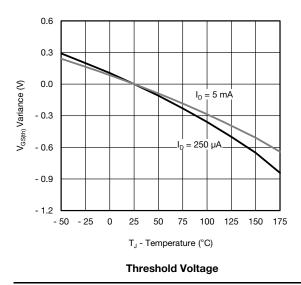
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

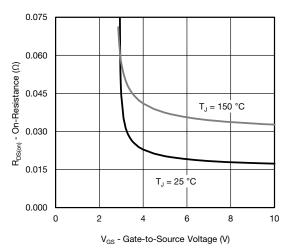


On-Resistance vs. Junction Temperature

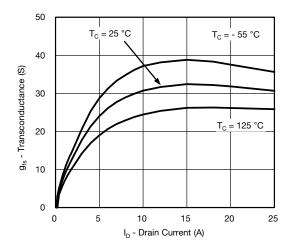


Source Drain Diode Forward Voltage

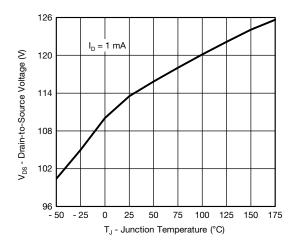




On-Resistance vs. Gate-to Source Voltage



Transconductance



Drain Source Breakdown vs. Junction Temperature

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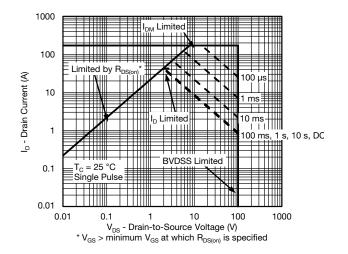
4

Document Number: 62846

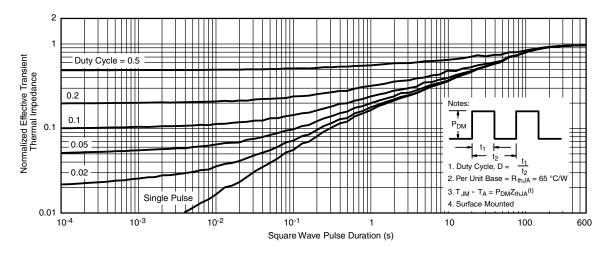
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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



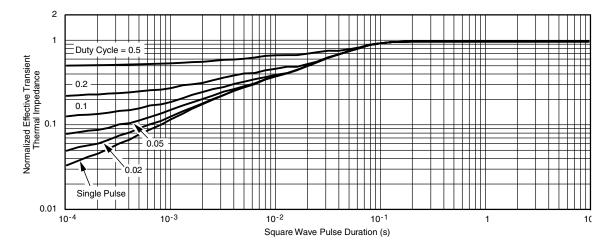
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62846.





PowerPAK[®] SO-8L

Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK SO-8L package:

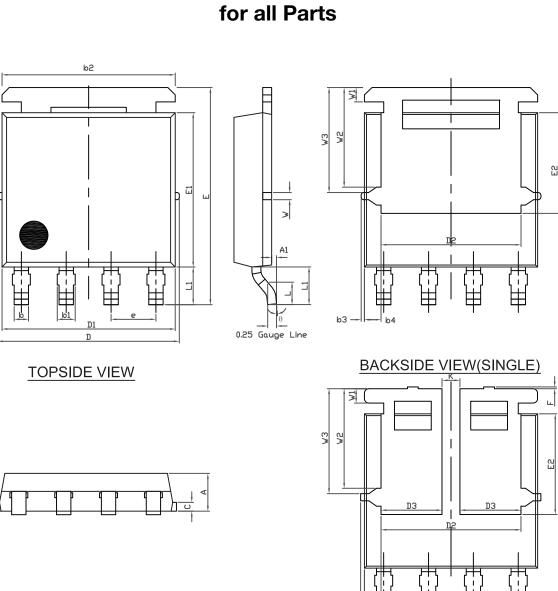
DATASHEET PART NUMBER	OLD ORDERING CODE ^a	NEW ORDERING CODE	
SQJ200EP	-	SQJ200EP-T1_GE3	
SQJ202EP	-	SQJ202EP-T1_GE3	
SQJ401EP	SQJ401EP-T1-GE3	SQJ401EP-T1_GE3	
SQJ402EP	SQJ402EP-T1-GE3	SQJ402EP-T1_GE3	
SQJ403EEP	SQJ403EEP-T1-GE3	SQJ403EEP-T1_GE3	
SQJ403EP	-	SQJ403EP-T1_GE3	
SQJ410EP	SQJ410EP-T1-GE3	SQJ410EP-T1_GE3	
SQJ412EP	SQJ412EP-T1-GE3	SQJ412EP-T1_GE3	
SQJ416EP	-	SQJ416EP-T1_GE3	
SQJ418EP	-	SQJ418EP-T1_GE3	
SQJ422EP	SQJ422EP-T1-GE3	SQJ422EP-T1_GE3	
SQJ423EP	_	SQJ423EP-T1_GE3	
SQJ431EP	SQJ431EP-T1-GE3	SQJ431EP-T1_GE3	
SQJ443EP	SQJ443EP-T1-GE3	SQJ443EP-T1_GE3	
SQJ444EP	_	SQJ444EP-T1_GE3	
SQJ446EP	-	SQJ446EP-T1_GE3	
SQJ456EP	SQJ456EP-T1-GE3	SQJ456EP-T1_GE3	
SQJ457EP	-	SQJ457EP-T1 GE3	
SQJ459EP	_	SQJ459EP-T1 GE3	
SQJ460AEP	_	SQJ460AEP-T1 GE3	
SQJ461EP	SQJ461EP-T1-GE3	SQJ461EP-T1_GE3	
SQJ463EP	SQJ463EP-T1-GE3	SQJ463EP-T1 GE3	
SQJ465EP	SQJ465EP-T1-GE3	SQJ465EP-T1_GE3	
SQJ469EP	SQJ469EP-T1-GE3	SQJ469EP-T1_GE3	
SQJ474EP	-	SQJ474EP-T1_GE3	
SQJ476EP	-	SQJ476EP-T1_GE3	
SQJ479EP	-	SQJ479EP-T1_GE3	
SQJ486EP	SQJ486EP-T1-GE3	SQJ486EP-T1_GE3	
SQJ488EP	SQJ488EP-T1-GE3	SQJ488EP-T1_GE3	
SQJ500AEP	SQJ500AEP-T1-GE3	SQJ488EP-T1_GE3	
SQJ840EP	SQJ840EP-T1-GE3	SQJ840EP-T1_GE3	
SQJ844AEP	SQJ844AEP-T1-GE3	SQJ844AEP-T1 GE3	
SQJ850EP	SQJ850EP-T1-GE3	SQJ850EP-T1 GE3	
SQJ858AEP	SQJ858AEP-T1-GE3	SQJ858AEP-T1_GE3	
SQJ856ALF SQJ868EP	-	SQJ868EP-T1_GE3	
SQJ886EP SQJ886EP	- SQJ886EP-T1-GE3	SQJ886EP-T1_GE3	
SQJ910AEP	SQJ910AEP-T1-GE3	SQJ910AEP-T1_GE3	
SQJ910AEP SQJ912AEP	SQJ910AEF-TT-GES SQJ912AEP-T1-GE3	SQJ910AEP-T1_GE3	
SQJ940EP	SQJ940EP-T1-GE3	SQJ912AEP-T1_GE3	
SQJ940EP SQJ942EP	SQJ940EP-11-GE3 SQJ942EP-T1-GE3	SQJ940EP-T1_GE3	
SQJ951EP	SQJ951EP-T1-GE3	SQJ951EP-T1_GE3	
SQJ952EP		SQJ952EP-T1_GE3	
SQJ956EP	SQJ956EP-T1-GE3	SQJ956EP-T1_GE3	
SQJ960EP	SQJ960EP-T1-GE3	SQJ960EP-T1_GE3	
SQJ963EP	SQJ963EP-T1-GE3	SQJ963EP-T1_GE3	
SQJ968EP	SQJ968EP-T1-GE3	SQJ968EP-T1_GE3	
SQJ980AEP	SQJ980AEP-T1-GE3	SQJ980AEP-T1_GE3	
SQJ992EP	SQJ992EP-T1-GE3	SQJ992EP-T1_GE3	

Note

a. Old ordering code is obsolete and no longer valid for new orders

Revision: 01-Jul-16





PowerPAK[®] SO-8L Case Outline

Revision: 07-Sep-15

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b3

BACKSIDE VIEW(DUAL)

Package Information



Vishay Siliconix

DIM	MILLIMETERS			INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX
А	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3		0.094	•		0.004	
b4		0.47			0.019	
С	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
е		1.27 BSC	•	0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	2.75	2.85	2.95	0.108	0.112	0.116
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
К		0.51	·		0.020	
W		0.23			0.009	
W1		0.41		0.016		
W2		2.82		0.111		
W3		2.96		0.117		
q	0°	-	10°	0°	-	10°

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



Vishay

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